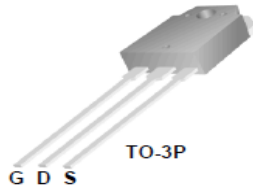


TS A65R300S1

650V 15A N-Channel SJ-MOSFET

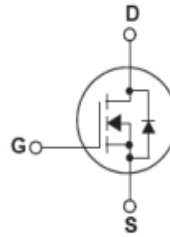
General Description

Truesemi SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance. This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.



Features

- 700V @TJ = 150 °C
- Typ. RDS(on) = 0.27Ω
- Ultra Low gate charge (typ. Qg = 43nC)
- 100% avalanche tested



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	650	V
I _D	Drain Current -Continuous (TC = 25°C) -Continuous (TC = 100°C)	15 9.4	A
I _{DM}	Drain Current – Pulsed (Note 1)	45	A
V _{GSS}	Gate-Source voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	284	mJ
I _{AR}	Avalanche Current (Note 1)	2.4	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	0.43	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
P _D	Power Dissipation (TC = 25°C)	104	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	1.2	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62	°C/W

Electrical Characteristics TC = 25℃ unless otherwise noted

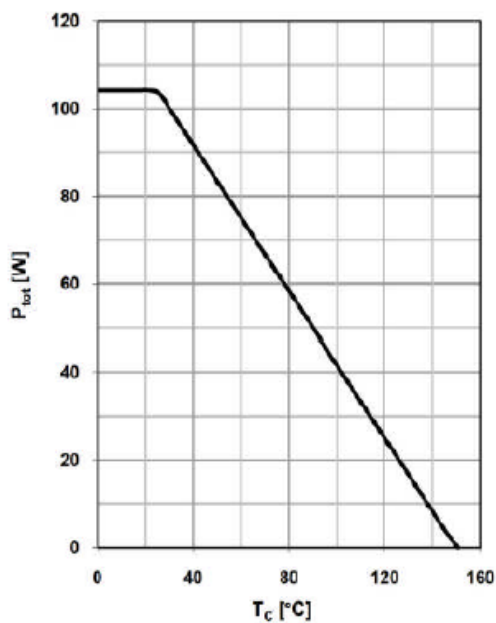
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25℃	650	--	--	V
		V _{GS} = 0V, I _D = 250μA, T _J = 150℃	--	700	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25℃	--	0.6	--	V/℃
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V -T _J = 150℃	--	-- 10	1 --	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.5	--	4.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 7.5A	--	0.27	0.3	Ω
g _{FS}	Forward Trans conductance	V _{DS} = 40V, I _D = 7.5A (Note 4)	--	16	--	S
R _g	Gate resistance	f = 1MHz, open drain	--	3.5	--	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	800	--	pF
C _{oss}	Output Capacitance		--	340	--	pF
C _{rss}	Reverse Transfer Capacitance		--	8	--	pF
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400V, I _D = 7.5A R _G = 20Ω(Note 4,5)	--	13	--	ns
t _r	Turn-On Rise Time		--	11	--	ns
t _{d(off)}	Turn-Off Delay Time		--	100	--	ns
t _f	Turn-Off Fall Time		--	12	--	ns
Q _g	Total Gate Charge	V _{DS} = 480V, I _D = 7.5A V _{GS} = 10V (Note 4,5)	--	43	--	nC
Q _{gs}	Gate-Source Charge		--	5	--	nC
Q _{gd}	Gate-Drain Charge		--	22	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	15	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	40	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _F = 7.5A	--	0.9	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _F = 7.5A di _F /dt =100A/μs (Note 4)	--	345	--	ns
Q _{rr}	Reverse Recovery Charge		--	4.5	--	μC

NOTES:

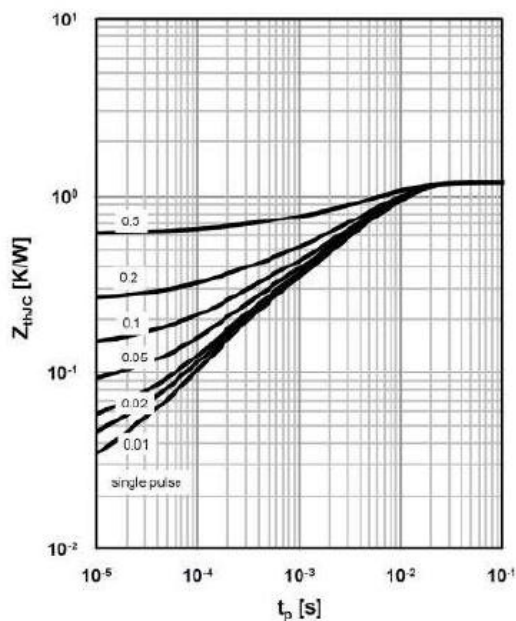
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS}=2.4A, V_{DD}=50V, Starting T_J=25℃
3. I_{SD}≤15A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25℃
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
- 5 Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

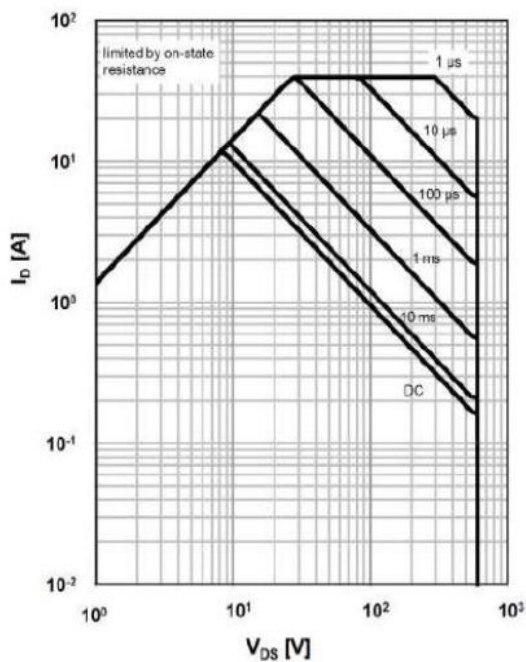
Power dissipation



Max. transient thermal impedance

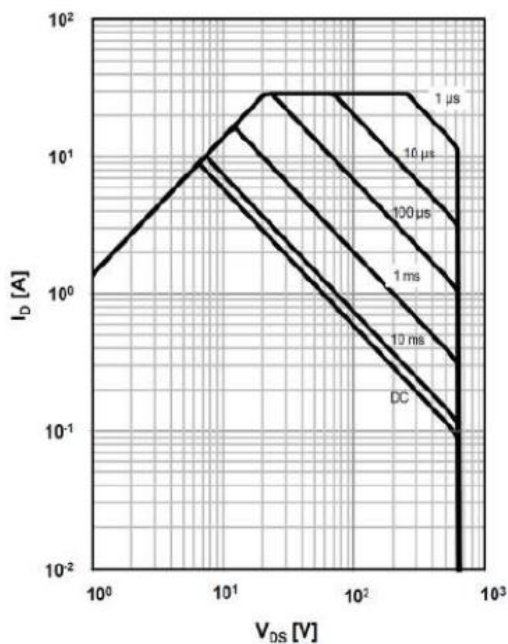


Safe operating area $T_C=25\text{ }^{\circ}\text{C}$



$I_D=f(V_{DS})$; $T_C=25\text{ }^{\circ}\text{C}$; $V_{GS} > 7\text{V}$;
 $D=0$; parameter t_p

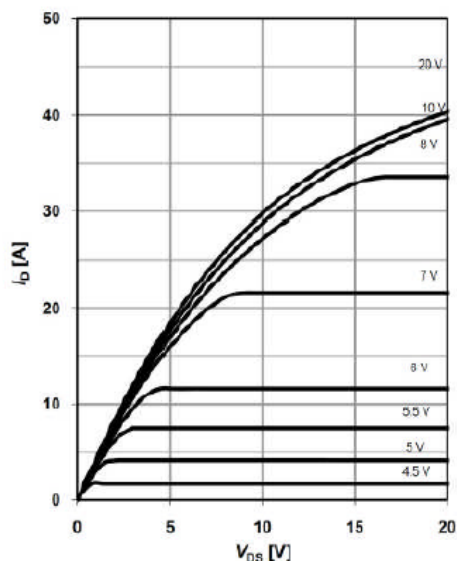
Safe operating area $T_C=80\text{ }^{\circ}\text{C}$



$I_D=f(V_{DS})$; $T_C=80\text{ }^{\circ}\text{C}$; $V_{GS} > 7\text{V}$;
 $D=0$; parameter t_p

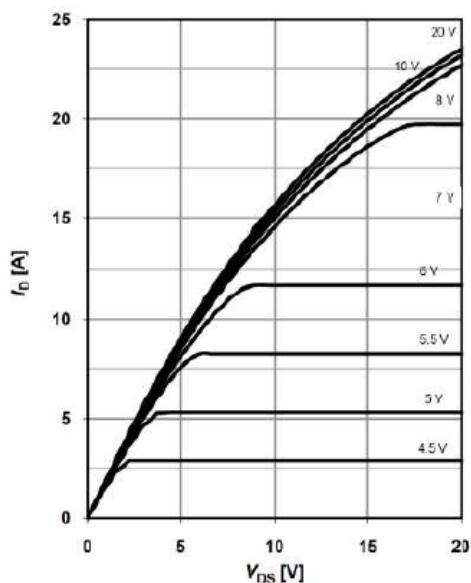
Typical Performance Characteristics

Typ. output characteristic



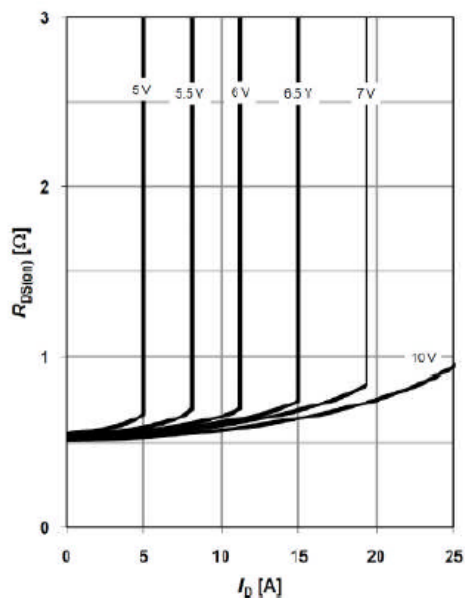
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$;
parameter $t_p = 10\mu\text{s}$, V_{GS}

Typ. output characteristic



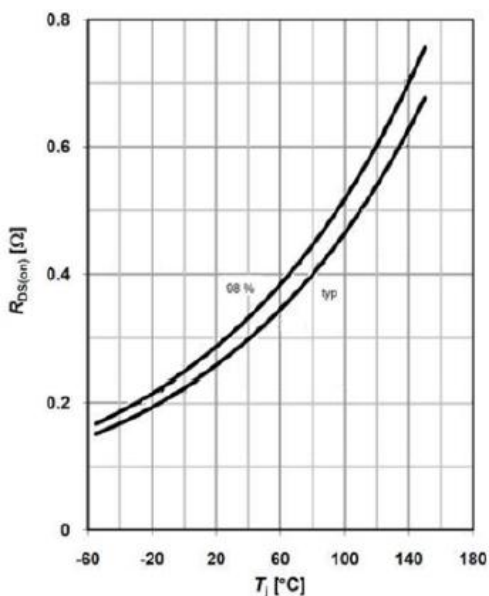
$I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$;
parameter $t_p = 10\mu\text{s}$, V_{GS}

Typ. Drain-Source on resistance



$R_{DS(on)} = f(I_D)$; $T_j = 125^\circ\text{C}$; parameter V_{GS}

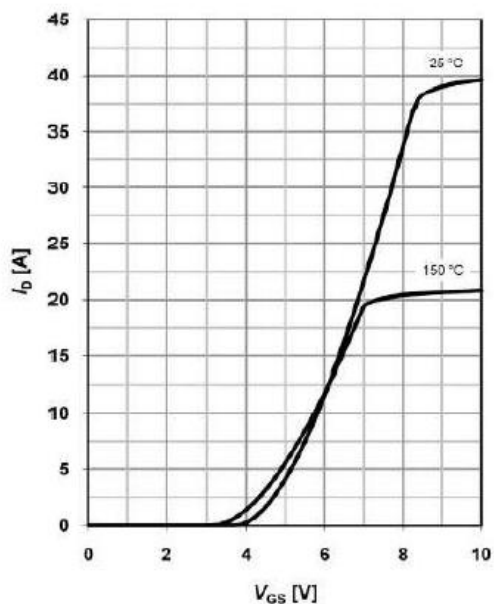
Typ. Drain-Source on resistance



$R_{DS(on)} = f(T_j)$; $T_j = 150^\circ\text{C}$; parameter
 $I_D = 4.4\text{A}$, $V_{GS} = 10\text{V}$

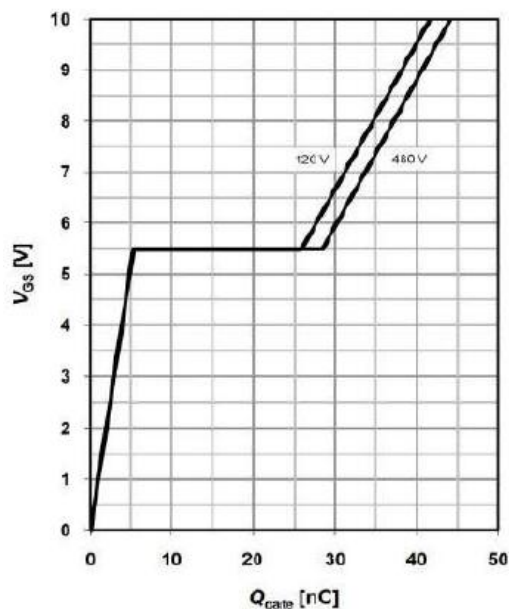
Typical Performance Characteristics

Typ. Transfer characteristic



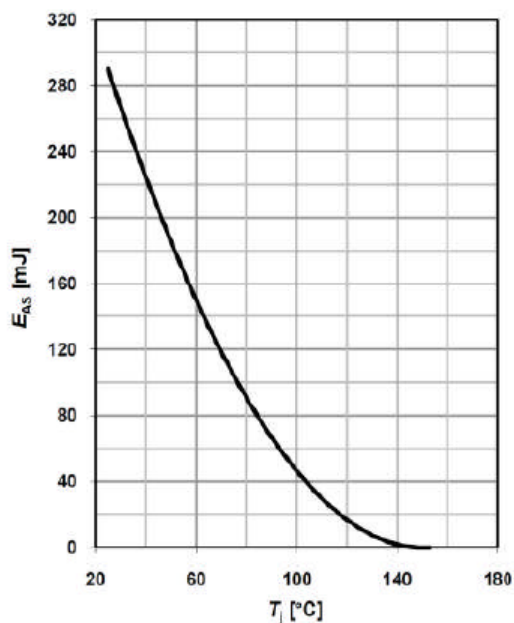
$I_D = f(V_{DS})$; $V_{DS} > 20V$;
parameter $t_p = 10\mu s$,

Typ. gate charge



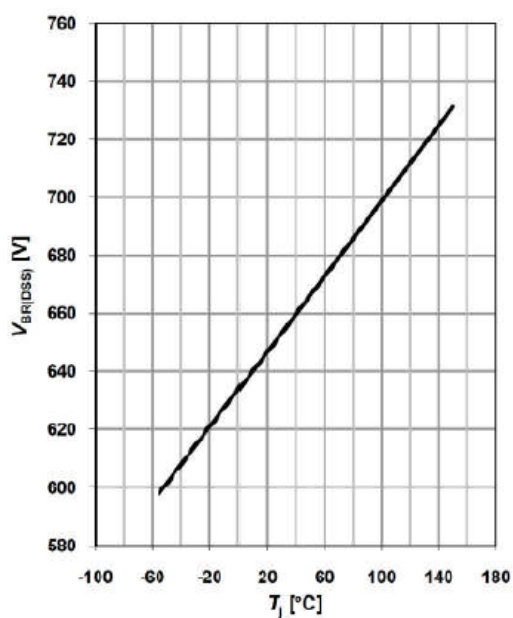
$V_{GS} = f(Q_g)$, $I_D = 4.4 A$ pulsed

Avalanche energy



$E_{AS} = f(T_j)$; $I_D = 2.4 A$; $V_{DD} = 50 V$

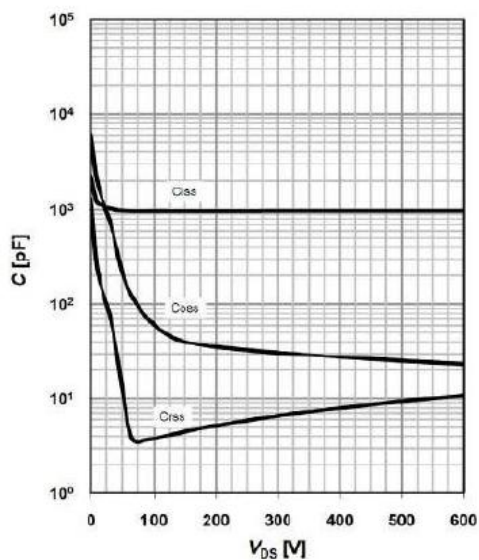
Drain-source breakdown voltage



$V_{BR(DSS)} = f(T_j)$; $I_D = 0.25mA$

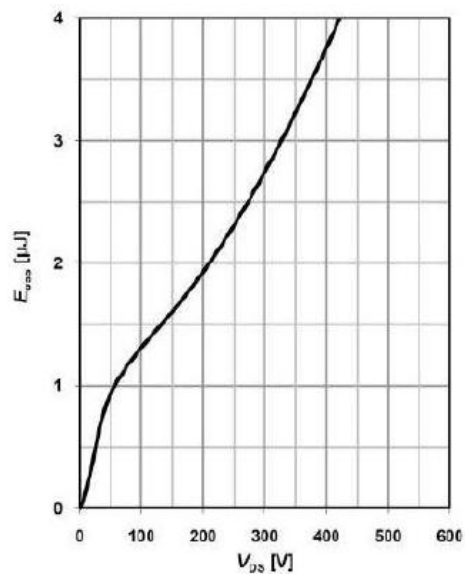
Typical Performance Characteristics

Typ. capacitances



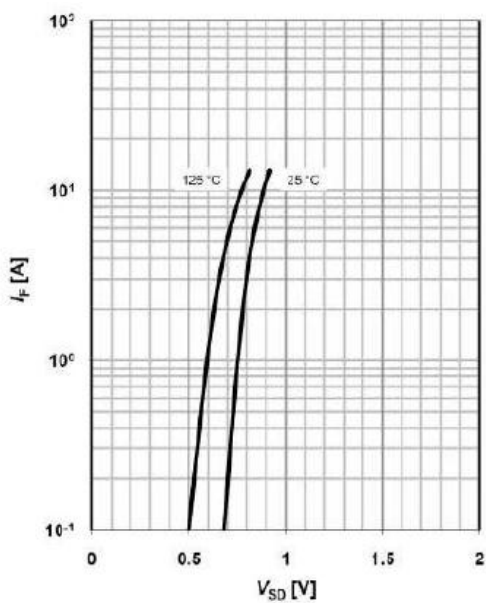
$$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$$

Typ. Coss stored energy



$$E_{OSS}=f(V_{DS})$$

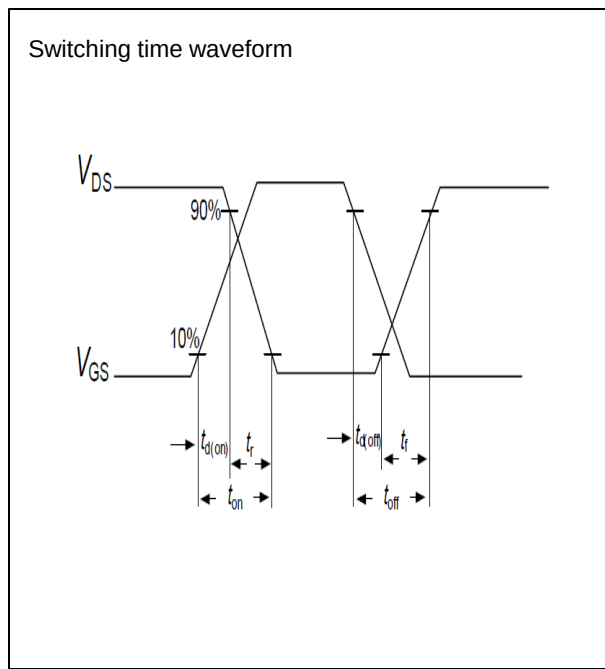
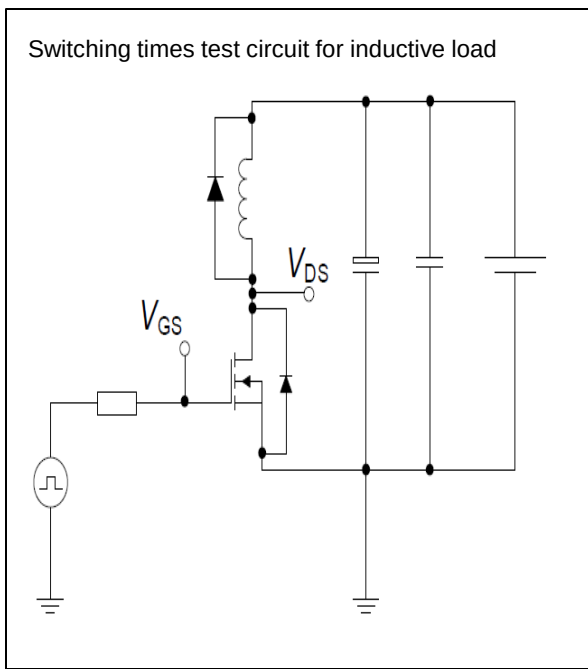
Forward characteristics of reverse diode



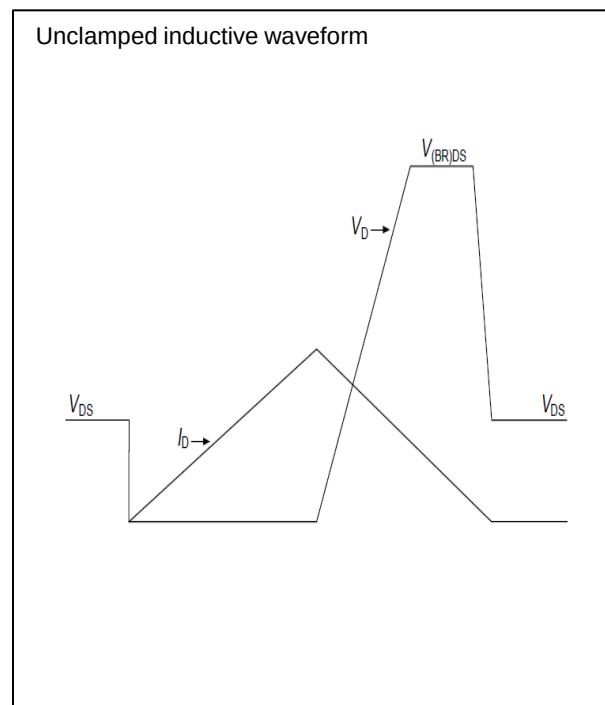
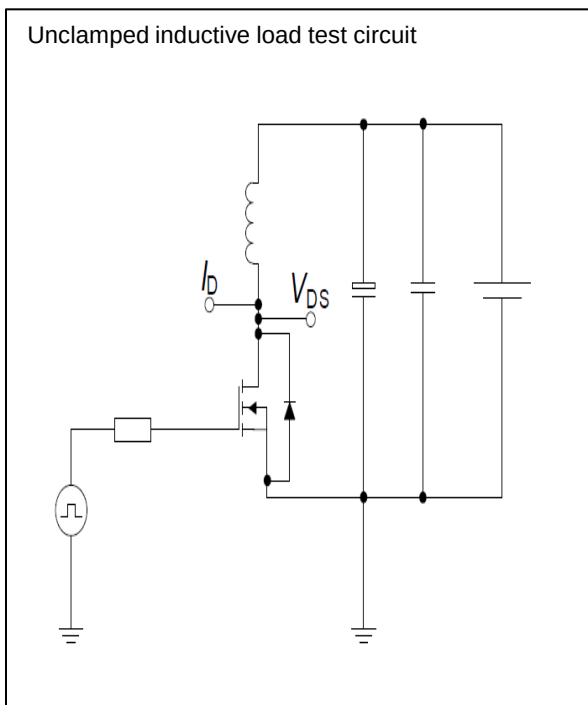
$$I_F=f(V_{SD}); \text{parameter: } T_j$$

Test circuits

Switching times test circuit and waveform for inductive load

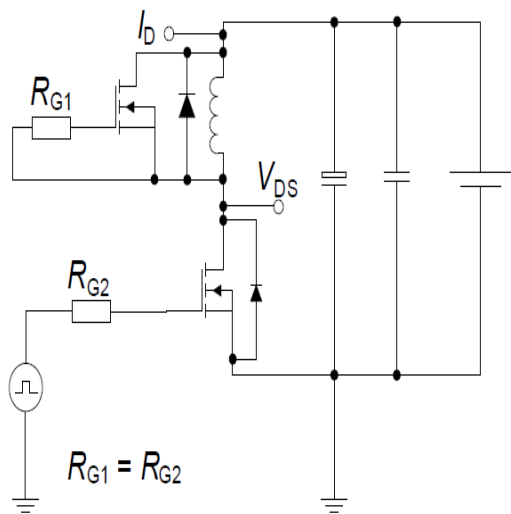


Unclamped inductive load test circuit and waveform



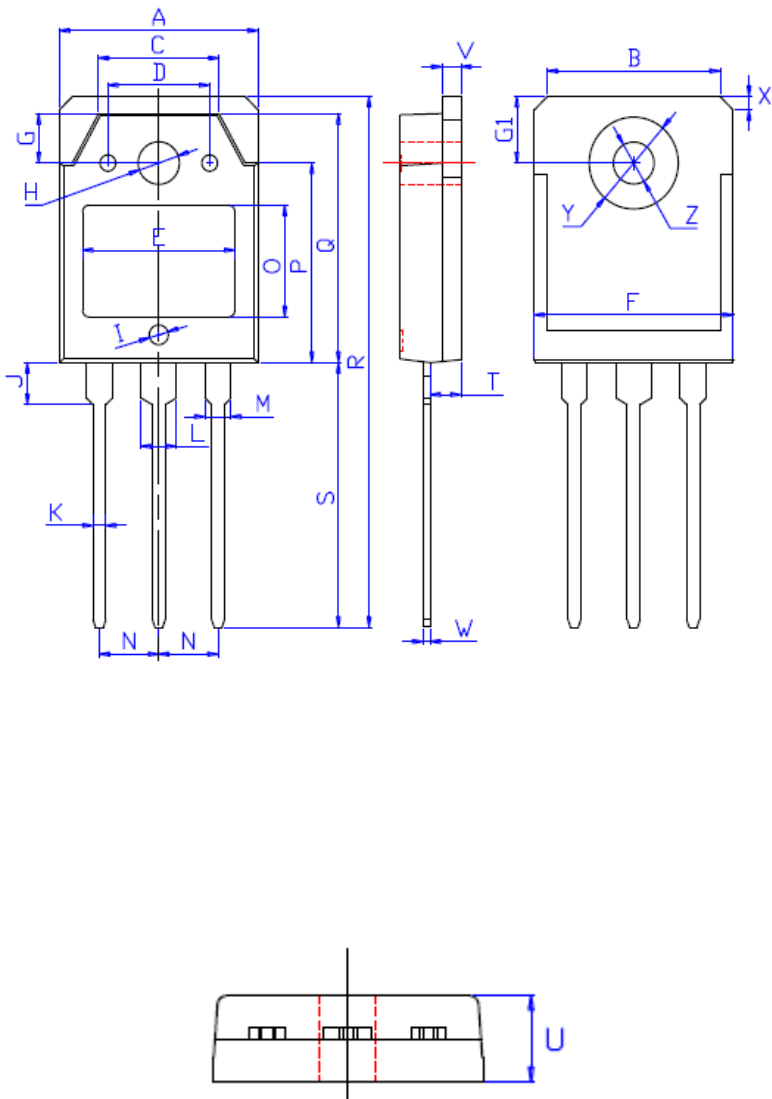
TSA65R300S1 650V 15A N-Channel SJ-MOSFET

Test circuit for diode characteristics



Package Outline TO-3P

TS465R300S1 650V 15A N-Channel SJ-MOSFET



DIM	MILLIMETERS
A	15.60±0.30
B	13.60±0.30
C	9.50±0.30
D	8.00±0.30
E	11.85±0.30
F	15.65±0.30
G	3.80±0.30
G1	5.00±0.30
H	Φ3.50±0.30
I	Φ1.50±0.30 深 0.15±0.15
J	3.20±0.30
K	1.00±0.15
L	3.10±0.15
M	2.10±0.15
N	5.45±0.30
O	8.40±0.30
P	13.90±0.30
Q	18.70±0.30
R	40.00±0.60
S	20.00±0.40
T	2.40±0.30
U	4.80±0.30
V	1.50±0.15
W	0.60±0.15
X	1.80±0.40
Y	7.00±0.30
Z	3.20±0.30